



BSS138AKA

60 V, single N-channel Trench MOSFET

6 February 2013

Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Very fast switching
- Trench MOSFET technology
- ESD protection
- Low threshold voltage
- AEC-Q101 qualified

3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j = 25\text{ }^\circ\text{C}$	-	-	60	V
V_{GS}	gate-source voltage		-20	-	20	V
I_D	drain current	$V_{GS} = 10\text{ V}; T_{amb} = 25\text{ }^\circ\text{C}$	[1]	-	200	mA
Static characteristics						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 100\text{ mA};$ pulsed; $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_j = 25\text{ }^\circ\text{C}$	-	2.7	4.5	Ω

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

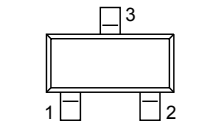
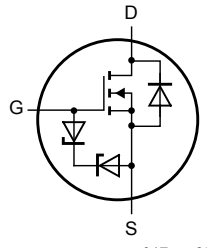


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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 <p>TO-236AB (SOT23)</p>	 <p>017aaa255</p>
2	S	source		
3	D	drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BSS138AKA	TO-236AB	plastic surface-mounted package; 3 leads	SOT23

7. Marking

Table 4. Marking codes

Type number	Marking code
BSS138AKA	%JL

[1] % = placeholder for manufacturing site code

8. Limiting values

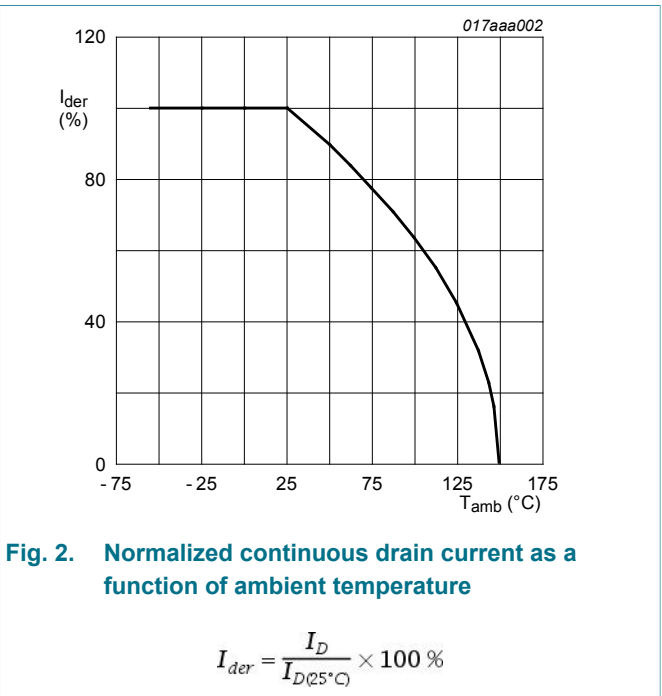
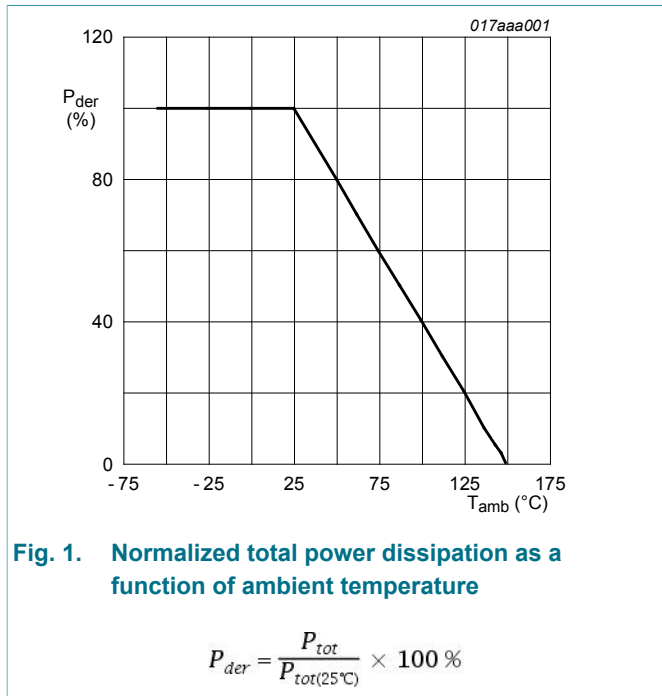
Table 5. Limiting values

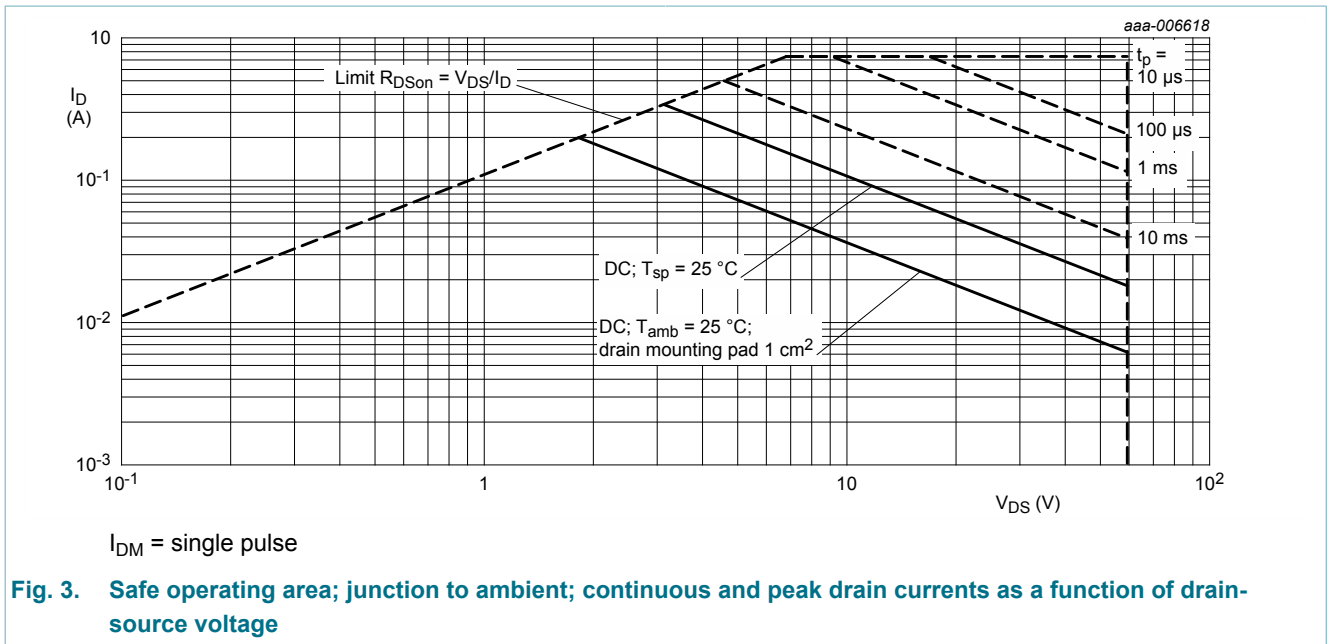
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	$T_j = 25\text{ °C}$		-	60	V
V_{GS}	gate-source voltage			-20	20	V
I_D	drain current	$V_{GS} = 10\text{ V}; T_{amb} = 25\text{ °C}$	[1]	-	200	mA
		$V_{GS} = 10\text{ V}; T_{amb} = 100\text{ °C}$	[1]	-	125	mA
I_{DM}	peak drain current	$T_{amb} = 25\text{ °C};$ single pulse; $t_p \leq 10\text{ }\mu\text{s}$		-	800	mA
P_{tot}	total power dissipation	$T_{amb} = 25\text{ °C}$	[2]	-	300	mW
			[1]	-	360	mW

Symbol	Parameter	Conditions	Min	Max	Unit
		$T_{sp} = 25\text{ °C}$	-	1060	mW
T_j	junction temperature		-55	150	°C
T_{amb}	ambient temperature		-55	150	°C
T_{stg}	storage temperature		-65	150	°C
Source-drain diode					
I_s	source current	$T_{amb} = 25\text{ °C}$	[1]	200	mA

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.





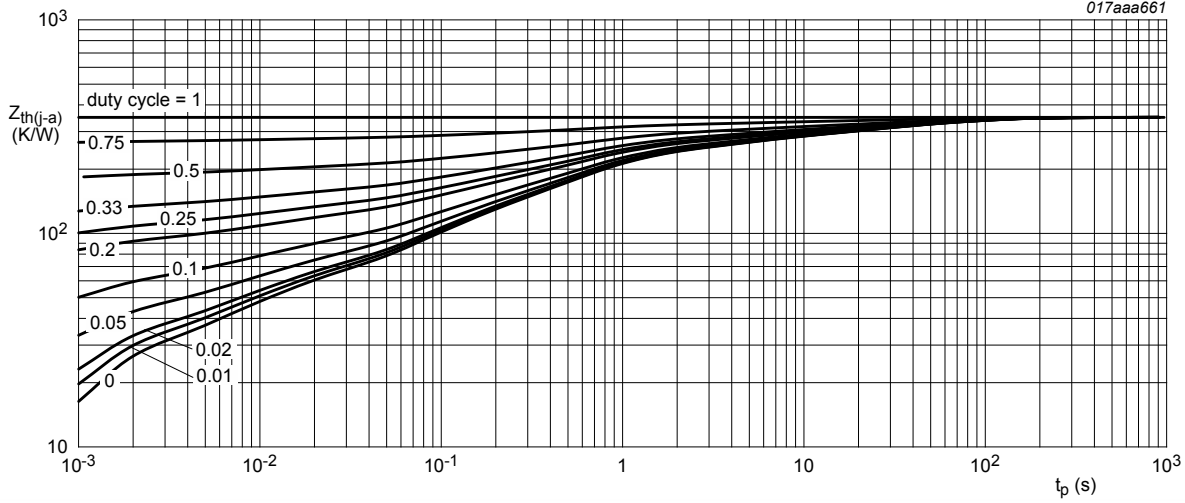
9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	350	400	K/W
			[2]	-	300	340	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	115	K/W

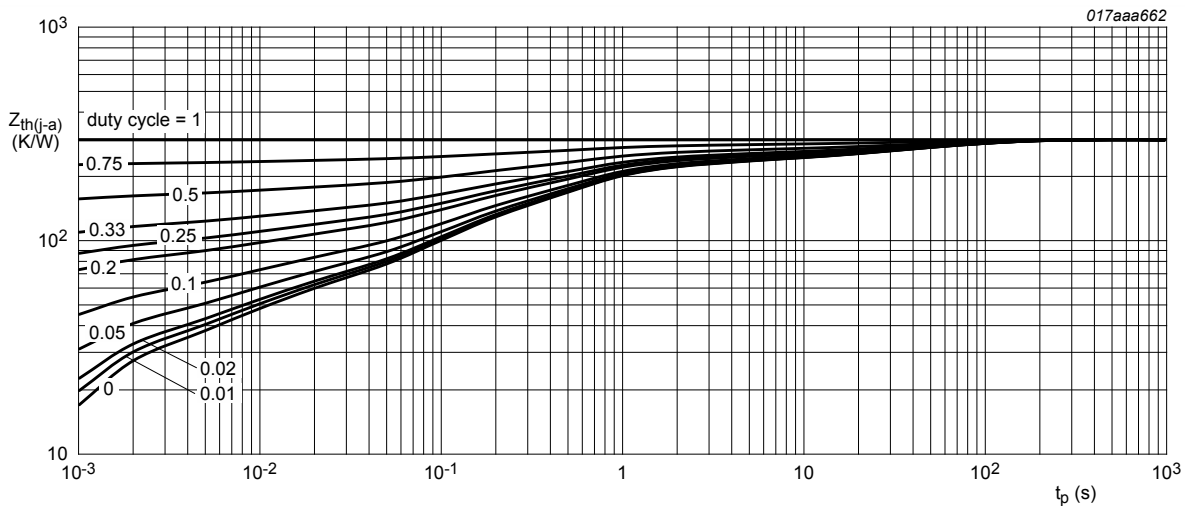
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm^2 .



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 1 cm²

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A$; $V_{GS} = 0 V$; $T_j = 25 \text{ }^\circ C$	60	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 A$; $V_{DS} = V_{GS}$; $T_j = 25 \text{ }^\circ C$	0.8	1.2	1.5	V
I_{DSS}	drain leakage current	$V_{DS} = 60 V$; $V_{GS} = 0 V$; $T_j = 25 \text{ }^\circ C$	-	-	1	μA
		$V_{DS} = 60 V$; $V_{GS} = 0 V$; $T_j = 150 \text{ }^\circ C$	-	-	10	μA

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	3.5	μA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-3.5	μA
		V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	1	μA
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-1	μA
		V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	0.5	μA
		V _{GS} = -4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-0.5	μA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 100 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _j = 25 °C	-	2.7	4.5	Ω
		V _{GS} = 10 V; I _D = 100 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _j = 150 °C	-	5.5	9.2	Ω
		V _{GS} = 4.5 V; I _D = 100 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _j = 25 °C	-	3	5.2	Ω
		V _{GS} = 2.5 V; I _D = 10 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _j = 25 °C	-	4	13	Ω
g _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 150 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _j = 25 °C	320	-	-	mS
Dynamic characteristics						
Q _{G(tot)}	total gate charge	V _{DS} = 30 V; I _D = 150 mA; V _{GS} = 4.5 V; T _j = 25 °C	-	0.39	0.51	nC
Q _{GS}	gate-source charge		-	0.1	-	nC
Q _{GD}	gate-drain charge		-	0.1	-	nC
C _{iSS}	input capacitance	V _{DS} = 30 V; f = 1 MHz; V _{GS} = 0 V; T _j = 25 °C	-	31	47	pF
C _{oSS}	output capacitance		-	21	-	pF
C _{rSS}	reverse transfer capacitance		-	16	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 40 V; R _L = 250 Ω; V _{GS} = 10 V; R _{G(ext)} = 6 Ω; T _j = 25 °C	-	5	10	ns
t _r	rise time		-	6	-	ns
t _{d(off)}	turn-off delay time		-	36	72	ns
t _f	fall time		-	22	-	ns
Source-drain diode						
V _{SD}	source-drain voltage	I _S = 115 mA; V _{GS} = 0 V; T _j = 25 °C	0.47	0.7	1.2	V

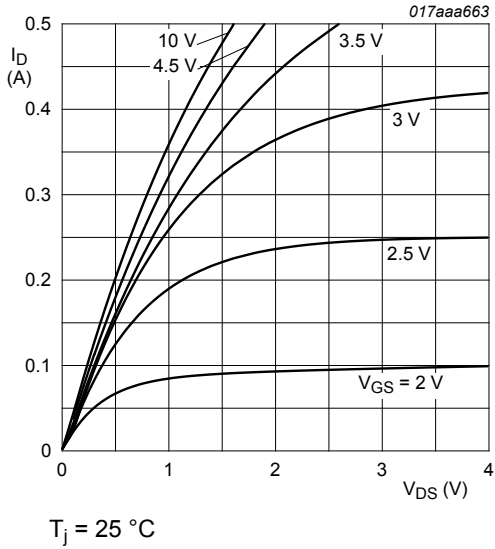


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

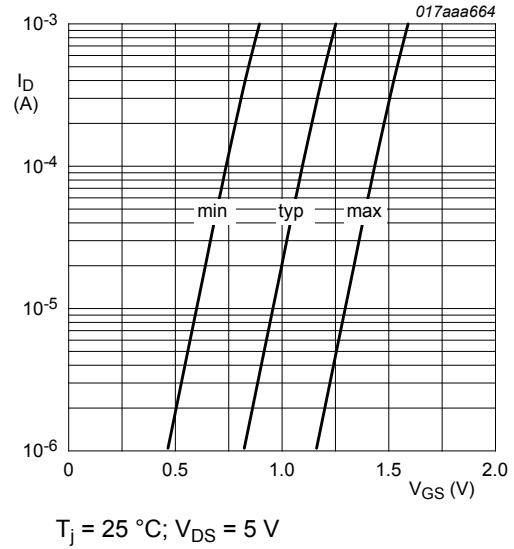


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

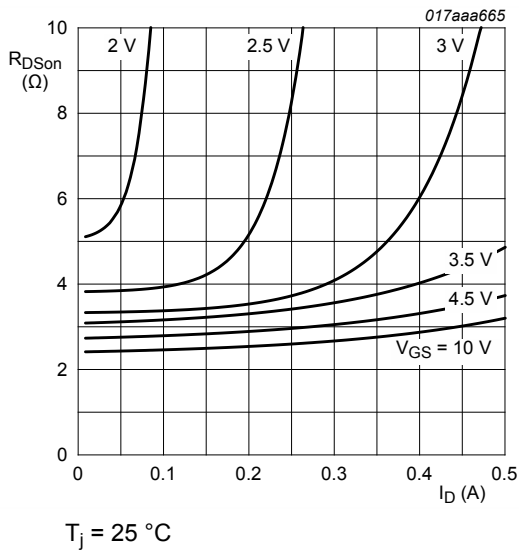


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

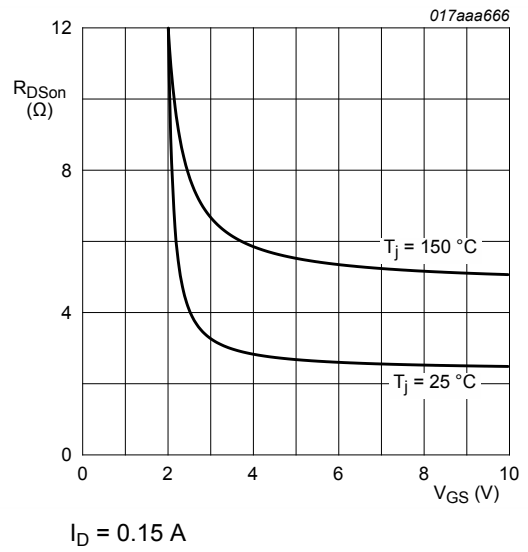
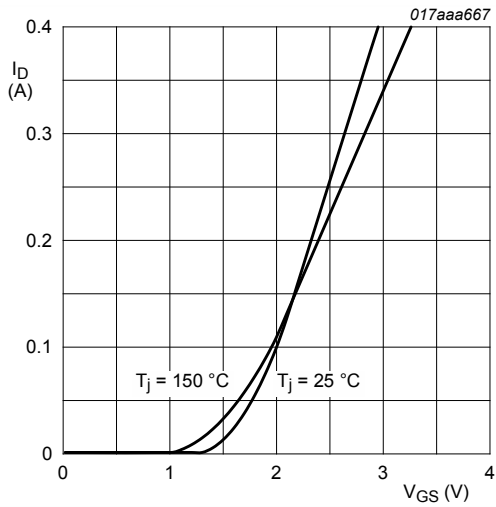


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values



$$V_{DS} > I_D \times R_{DSon}$$

Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

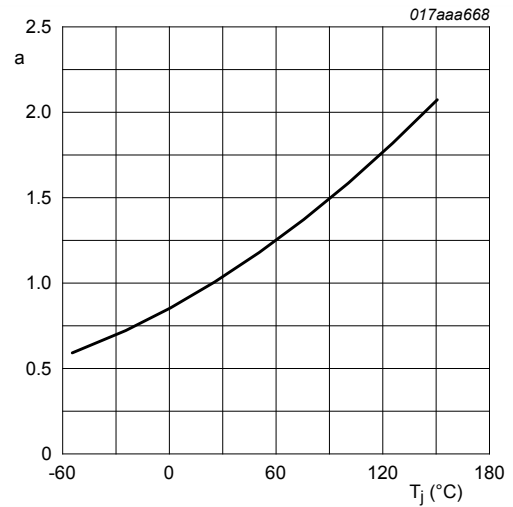
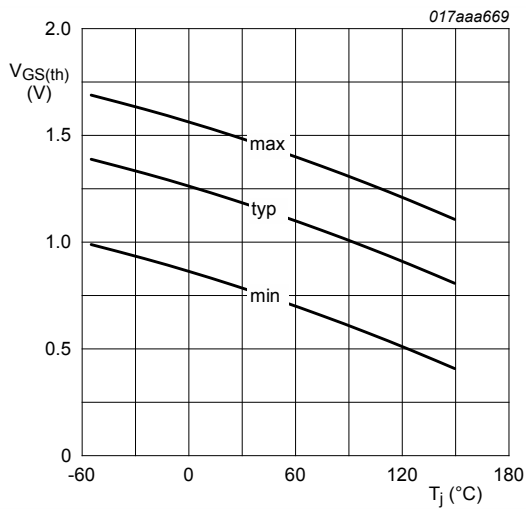


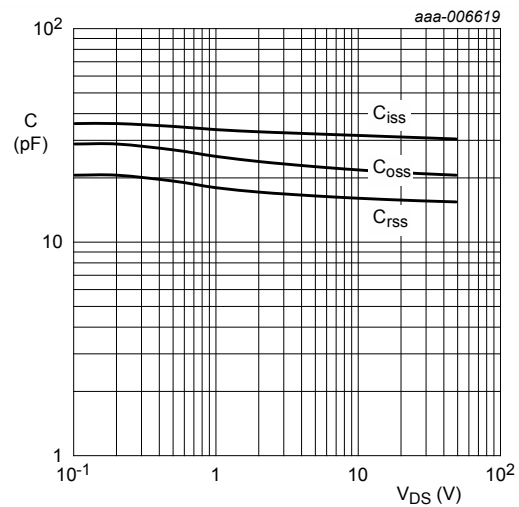
Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^\circ C)}}$$



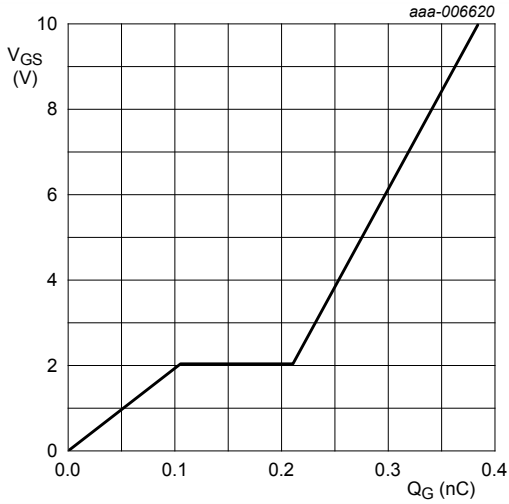
$$I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$$

Fig. 12. Gate-source threshold voltage as a function of junction temperature



$$f = 1 \text{ MHz}; V_{GS} = 0 \text{ V}$$

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$I_D = 150 \text{ mA}; V_{DS} = 30 \text{ V}; T_{amb} = 25 \text{ }^\circ\text{C}$

Fig. 14. Gate-source voltage as a function of gate charge; typical values

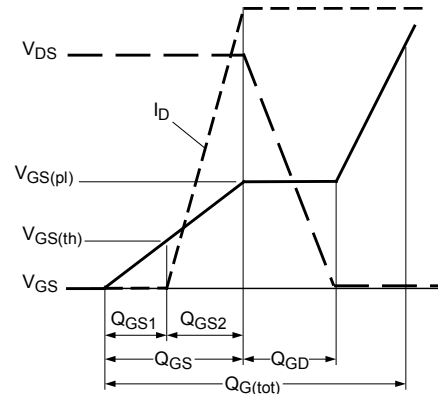
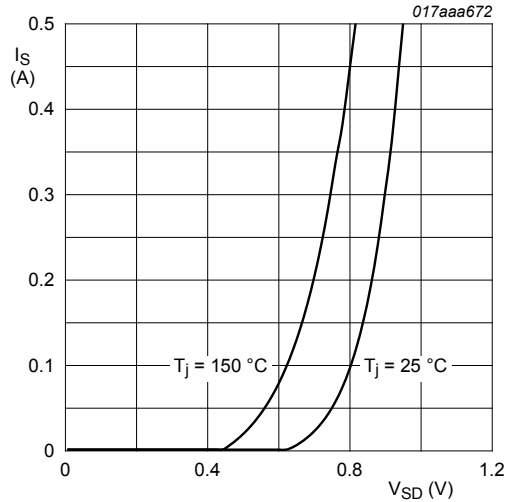


Fig. 15. Gate charge waveform definitions



$V_{GS} = 0 \text{ V}$

Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

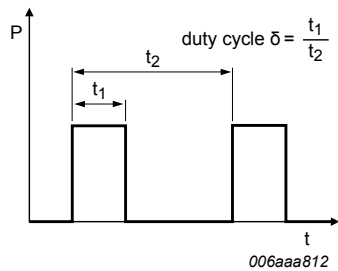


Fig. 17. Duty cycle definition

11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline

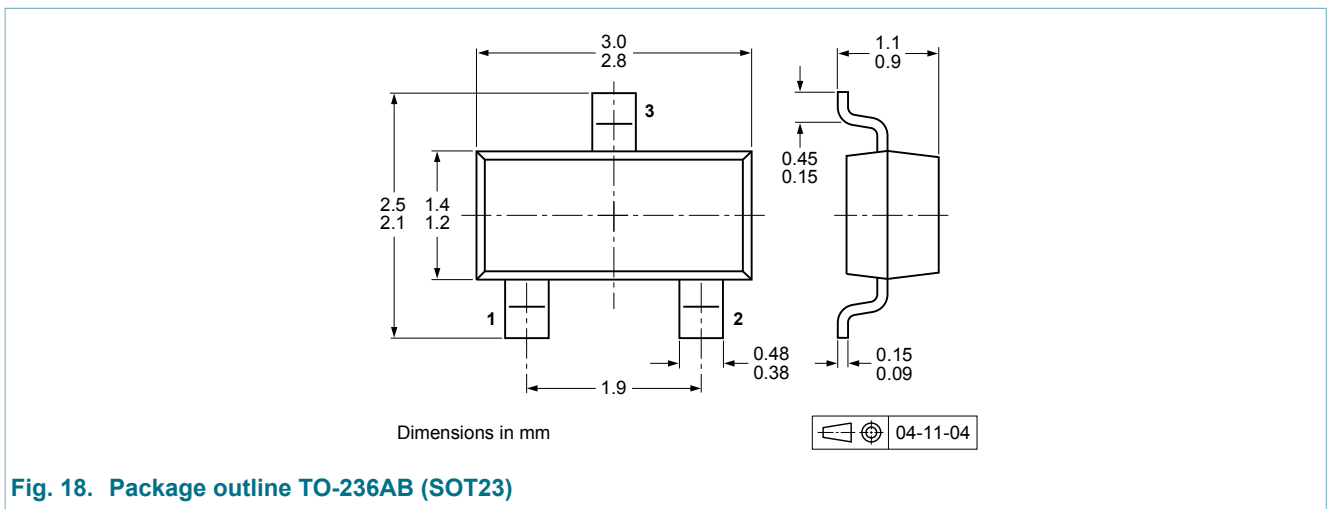


Fig. 18. Package outline TO-236AB (SOT23)

13. Soldering

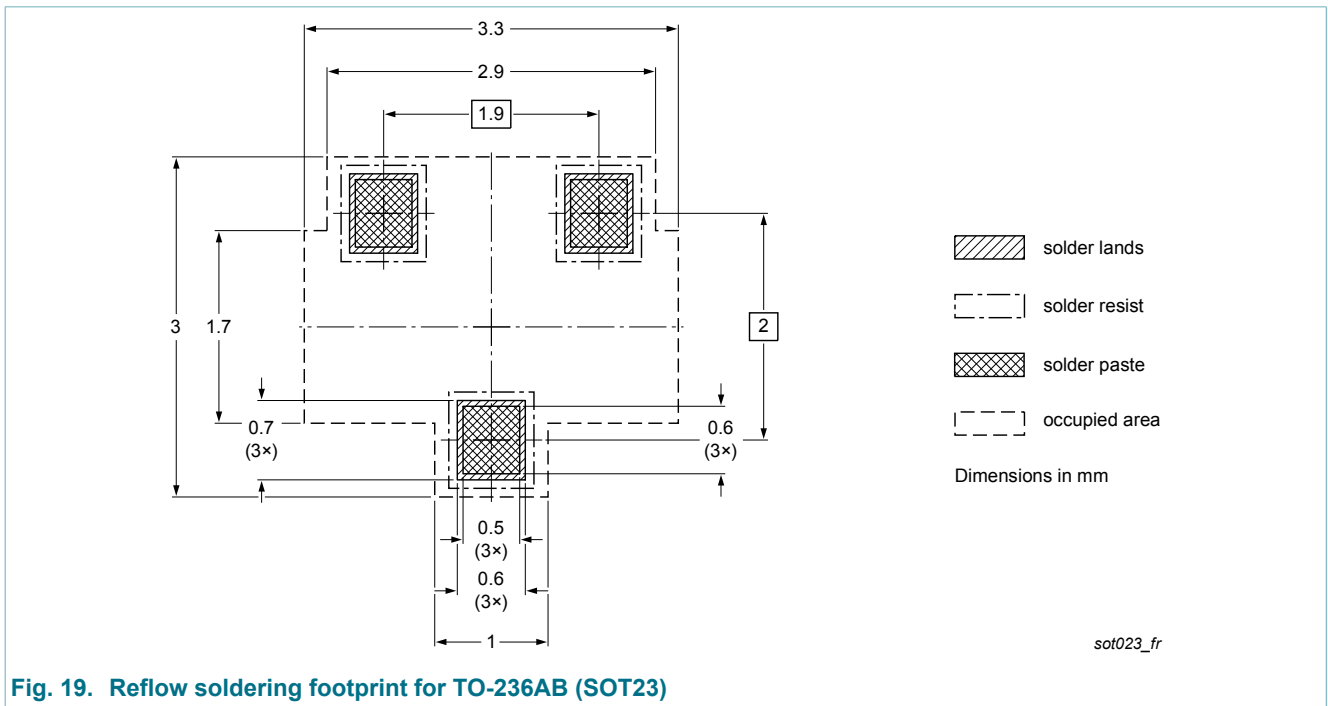


Fig. 19. Reflow soldering footprint for TO-236AB (SOT23)

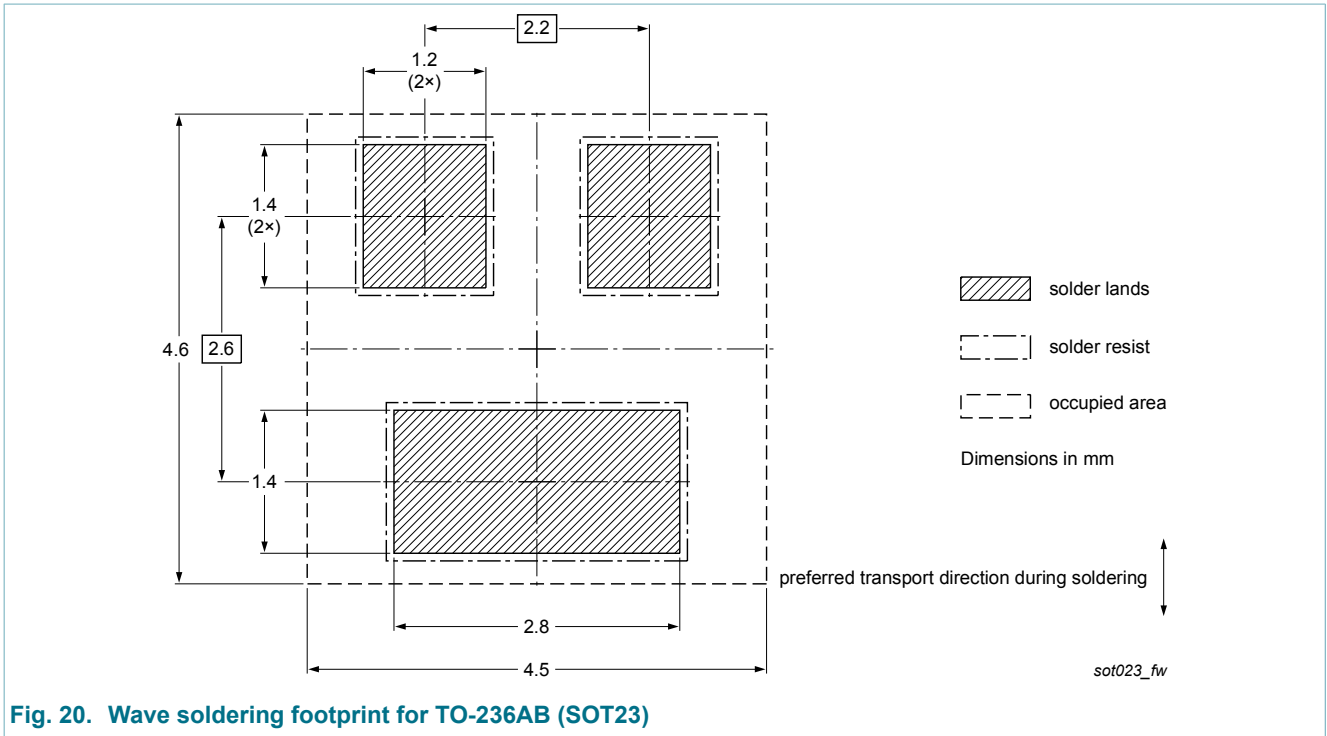


Fig. 20. Wave soldering footprint for TO-236AB (SOT23)

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
BSS138AKA v.1	20130206	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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16. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	2
9	Thermal characteristics	4
10	Characteristics	5
11	Test information	9
11.1	Quality information	
12	Package outline	10
13	Soldering	10
14	Revision history	11
15	Legal information	12
15.1	Data sheet status	12
15.2	Definitions	12
15.3	Disclaimers	12
15.4	Trademarks	13

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